



Bipolar NPN Bare Die – BTN6057

Part Description

The BTN6057 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 80V
- VCEO = 50V
- VEBO = 6V
- hFE = 200-560 @ VCE = 2V, IC = 0.5A
- VCE(Sat) = 0.24V @ IC = 2A, IB = 100mA
- fT = 400 MHz @ VCE = 10V, IE = 0A
- COBO = 15pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to SANYO 2SC5706 or ROHM 2SC5103

Die Size (Unseen)

940µm X 940µm, 37 Mils X 37 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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